ABSTRACT OF THE DISCLOSURE

A method of producing a device with a ferroelectric crystal thin film on a first substrate comprises the steps of providing a ferroelectric crystal, of irradiating a first surface of said ferroelectric crystal with ions so that a damaged layer is created underneath said first surface, of bonding a block of material including said first substrate to said ferroelectric crystal to create a bonded element, wherein an interface is formed between said first surface and a second surface of said block, and of heating the bonded element and separating it at the damaged layer, so that a ferroelectric crystal layer remains supported by the first substrate. By this method, very thin films – down to thicknesses a fraction of a micrometer – of ferroelectric crystals may be fabricated without jeopardizing the monocrystalline structure. According to a preferred embodiment, prior to bonding the block to the second substrate, the first substrate is provided with a electrode layer prior to the bonding. In this way, a thin ferroelectric crystal layer may even be subjected to an applied voltage by electrodes.

(Fig. 1)